

PRELIMINARY

Notice: This is not a final specification.
Some parametric limits are subject to change.

MITSUBISHI LASER DIODES
ML8XX2 SERIES

InGaAs — MQW HIGH POWER LASER DIODES

TYPE
NAME

ML8XX2

DESCRIPTION

ML8XX2 series are InGaAs high power laser diodes which provides a stable, single transverse mode oscillation with emission wavelength of 980nm and standard continuous light output of 150mW.

FEATURES

- High power (CW 150mW)
 - 980nm typical emission wavelength
 - Stable single transverse mode oscillation
 - MQW* active layer
- *: Multiple Quantum Well

APPLICATION

Optical fiber amplifier

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Conditions	Ratings	Unit
P _o	Light output power	CW	180	mW
I _F	Forward current	CW	350	mA
T _c	Case temperature	—	+20~+30	°C
T _{stg}	Storage temperature	—	-40~+100	°C

ELECTRICAL/OPTICAL CHARACTERISTICS (T_c = 25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
I _{th}	Threshold current	CW	—	20	50	mA
I _{OP}	Operating current	CW, P _o = 150mW	—	200	260	mA
V _{OP}	Operating voltage	CW, P _o = 150mW	—	2.0	2.5	V
λ _c	Center wavelength	CW, P _o = 150mW	970	980	990	nm
Δλ	Spectral width	CW, P _o = 150mW, RMS	—	0.3	2	nm
θ	Beam divergence angle (parallel)	CW, P _o = 150mW	5	8	15	deg.
θ _⊥	Beam divergence angle (perpendicular)	CW, P _o = 150mW	30	35	40	deg.

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TYPICAL CHARACTERISTICS

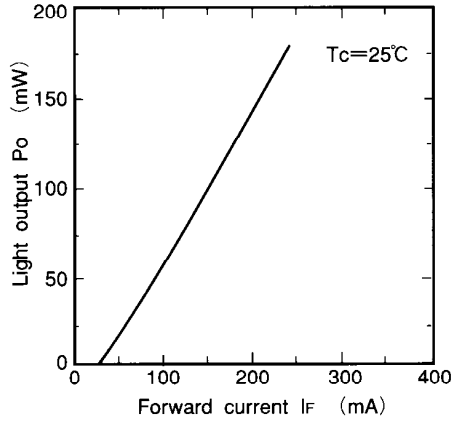


Fig.1 Light output vs. forward current

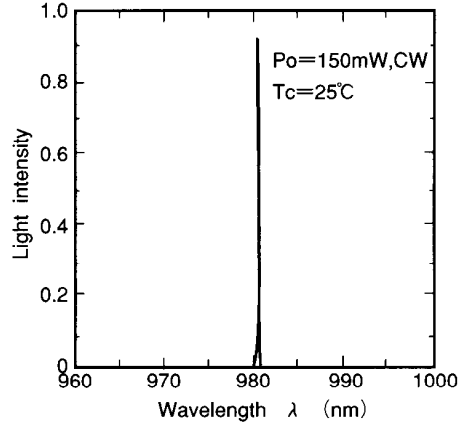


Fig.2 Spectrum

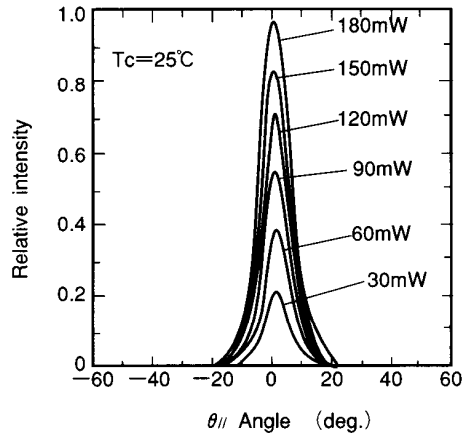
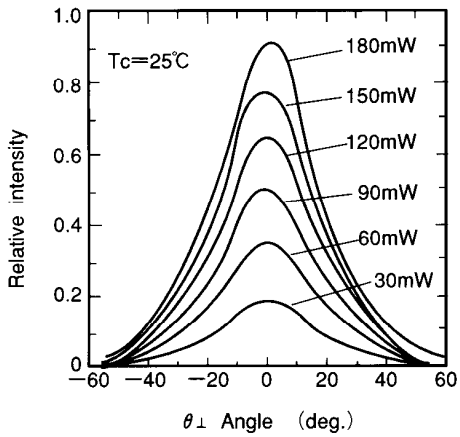


Fig.3 Far field patterns